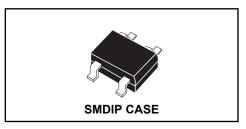
CBR1F-D020S SERIES

1.0 AMP DUAL IN LINE FAST RECOVERY SILICON BRIDGE RECTIFIER





DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBR1F-D020S Series types are fast recovery, full wave bridge rectifiers mounted in a durable epoxy surface mount molded case, utilizing glass passivated chips. To order devices on tape and reel (1,000/13" reel) add TR13 suffix.

MARKING CODE: FULL PART NUMBER

 $\textbf{MAXIMUM RATINGS:} \ \, (\text{T}_{A}\text{=}25^{\circ}\text{C unless otherwise specified})$

	SYMBOL	CBR1F- <u>D020S</u>	CBR1F- <u>D040S</u>	CBR1F- <u>D060S</u>	CBR1F- <u>D080S</u>	CBR1F- <u>D100S</u>	<u>UNITS</u>
Peak Repetitive Reverse Voltage	V_{RRM}	200	400	600	800	1000	V
DC Blocking Voltage	V_{R}	200	400	600	800	1000	V
RMS Reverse Voltage	V _{R(RMS)}	140	280	420	560	700	V
Average Forward Current (T _A =40°C)	IO			1.0			Α
Peak Forward Surge Current	I_{FSM}			50			Α
Rating for Fusing (t<8.35ms)	l ² t			3.74			A^2s
Operating and Storage Junction Temperature	T _J ,T _{stg}			-65 to +150	0		°C

ELECTRICAL CHARACTERISTICS PER DIODE (TA=25°C unless otherwise noted)

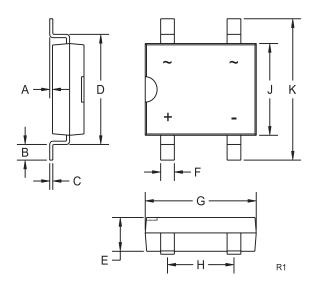
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _R	V _R =Rated V _{RRM}			5.0	μΑ
I_{R}	V _R =Rated V _{RRM} , T _A =125°C			0.5	mA
V _F	I _F =1.0A			1.3	V
t _{rr} (200V thru 400V)	I_F =0.5A, I_R =1.0A, Recov. to 0.25A			200	ns
t _{rr} (600V)	I_F =0.5A, I_R =1.0A, Recov. to 0.25A			300	ns
t _{rr} (800V, 1000V)	I_F =0.5A, I_R =1.0A, Recov. to 0.25A			500	ns
CJ	V _R =4.0V, f=1.0MHz		25		pF



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SMDIP CASE - MECHANICAL OUTLINE



DIMENSIONS						
	INC	HES	MILLIMETERS			
SYMBOL	MIN	MAX	MIN	MAX		
Α	0.004	0.008	0.10	0.20		
В	0.040	0.060	1.02	1.52		
C	0.009		0.23			
D	0.290	0.310	7.37	7.87		
E	0.086	0.098	2.18	2.49		
F	0.038	0.042	0.97	1.07		
G	0.316	0.335	8.03	8.51		
Ι	0.195	0.205	4.95	5.21		
J	0.245	0.255	6.22	6.48		
K	0.360	0.410	9.14	10.41		

SMDIP (REV: R1)

MARKING CODE: FULL PART NUMBER

R0 (14-January 2003)